

Turkish Journal of Physics

Turkish Journal

of

Physics

Characterization of Thin Film Al/p-CdTe Schottky Diode

M. G. MAHESHA, V. B. KASTURI and G. K. SHIVAKUMAR
Department of Physics, National Institute of Technology Karnataka, Surathkal,
Srinivasnagar, 575 025 INDIA
e-mail: gskskrec@yahoo.com

 [Keywords](#)
 [Authors](#)

Abstract: A study has been made on the behavior of Al/p-CdTe thin film junction grown by thermal evaporation method. I-V characteristics show that the Al makes Schottky contact with p-CdTe. The variation of junction capacitance with frequency and voltage has been studied to evaluate the barrier height. The activation energy and band gap have been estimated by studying variation of resistivity with temperature. Using all these data, band diagram of Al/p-CdTe has been proposed.

Key Words: Al, p-CdTe, Schottky, C-V, band diagram



phys@tubitak.gov.tr

[Scientific Journals Home](#)
[Page](#)

Turk. J. Phys., **32**, (2008), 151-156.

Full text: [pdf](#)

Other articles published in the same issue: [Turk. J. Phys.,vol.32,iss.3.](#)